To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD1527

Silicon NPN Triple Diffused

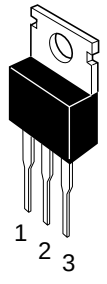
ADE-208-913 (Z)
1st. Edition
September 2000

Application

High voltage power amplifier

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

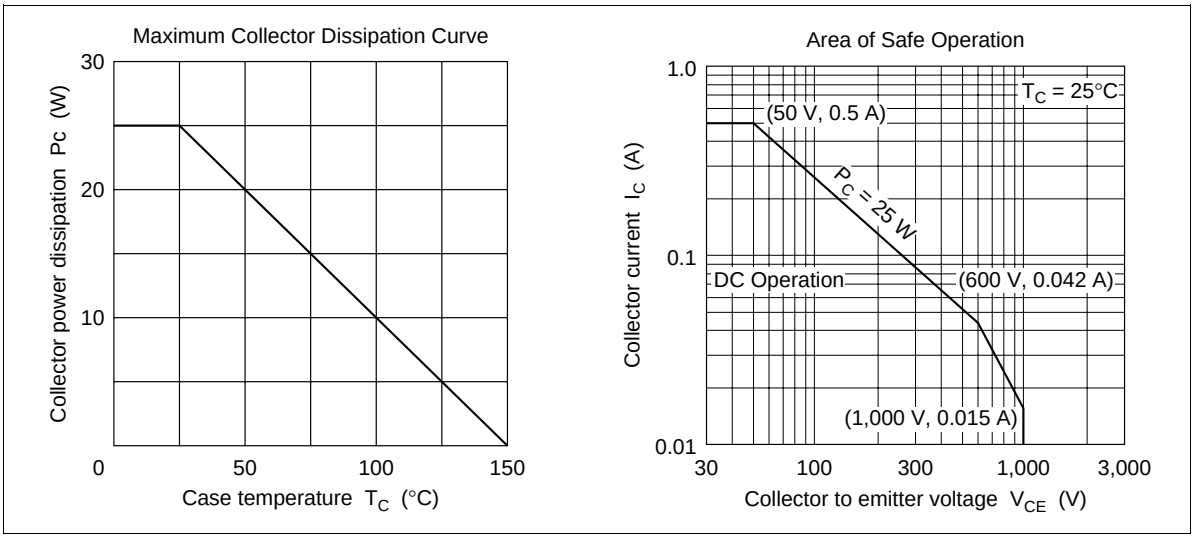
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	1000	V
Collector to emitter voltage	V_{CEO}	1000	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	0.5	A
Collector power dissipation	P_C	1.8	W
	P_C*[1]	25	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

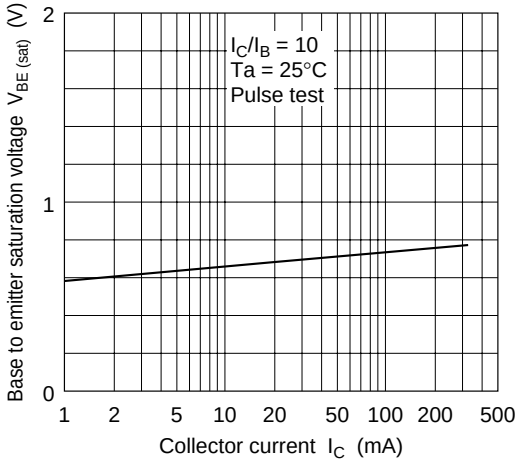
Note: 1. Value at T_C = 25°C.

Electrical Characteristics (Ta = 25°C)

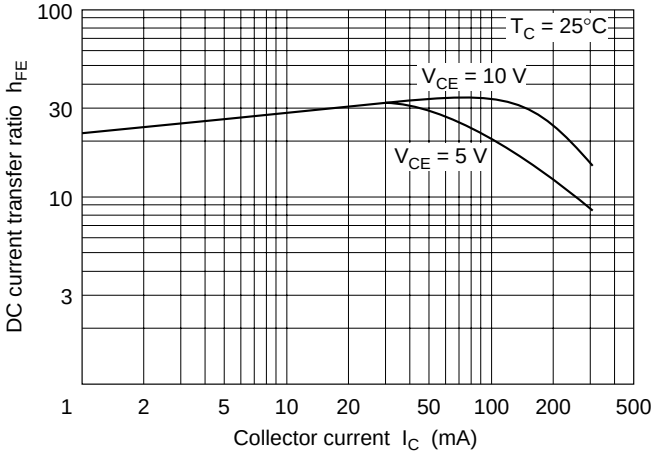
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	1000	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	I_E = 1 mA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	10	µA	V_{CB} = 800 V, I_E = 0
DC current transfer ratio	h_{FE1}	10	—	—		V_{CE} = 5 V, I_C = 10 mA
	h_{FE2}	10	—	—		V_{CE} = 5 V, I_C = 100 mA
Base to emitter voltage	V_{BE}	—	—	1.2	V	V_{CE} = 5 V, I_C = 100 mA
Collector to emitter saturation voltage	$V_{CE\ (sat)}$	—	—	5	V	I_C = 300 mA, I_B = 60 mA
Gain bandwidth product	f_T	—	5	—	MHz	V_{CE} = 20 V, I_C = 50 mA
Collector output capacitance	Cob	—	5	—	pF	V_{CB} = 100 V, I_E = 0, f = 1 MHz



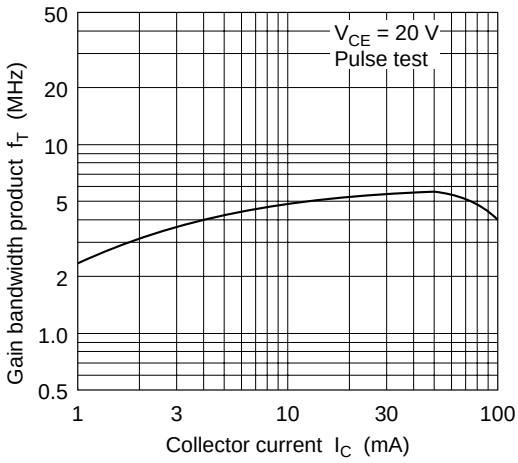
Base to Emitter Saturation Voltage
vs. Collector Current



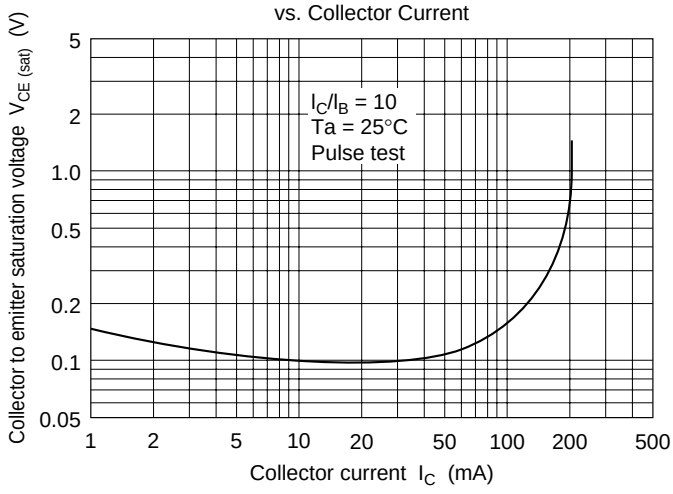
DC Current Transfer Ratio
vs. Collector Current

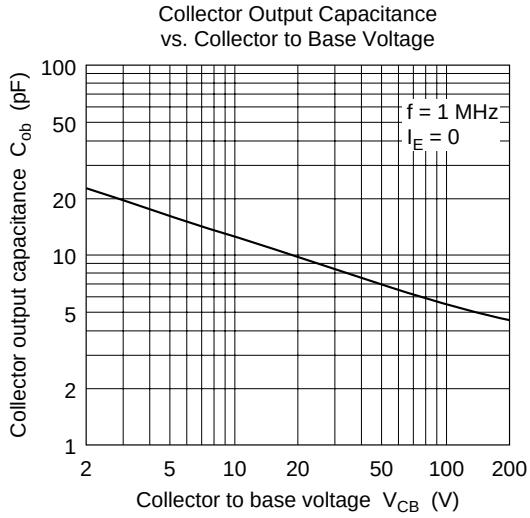


Gain Bandwidth Product
vs. Collector Current



Collector to Emitter Saturation Voltage
vs. Collector Current




Collector Output Capacitance
vs. Collector to Base Voltage
Collector output capacitance C_{ob} (pF)
100
50
20
10
5
2
1
f = 1 MHz
I_E = 0
2
5
10
20
50
100
200
Collector to base voltage V_{CB} (V)

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